

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	PATENT APPLICATION
)	
Inventors: Fengyan Zhang, Wei-Wei Zhuang))	
and Sheng Teng Hsu)	
)	
Serial No.: Not Yet Assigned)	Attorney Docket No.
)	SLA 0642
Filed: Herewith)	
)	
Title: BUFFER LAYERS TO ENHANCE))	
THE C-AXIS GROWTH OF)	
Bi ₄ Ti ₃ O ₁₂ THIN FILM ON HIGH)	
TEMPERATURE IRIIDIUM)	
<u>COMPOSITE ELECTRODE</u>)	

Honorable Commissioner for Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

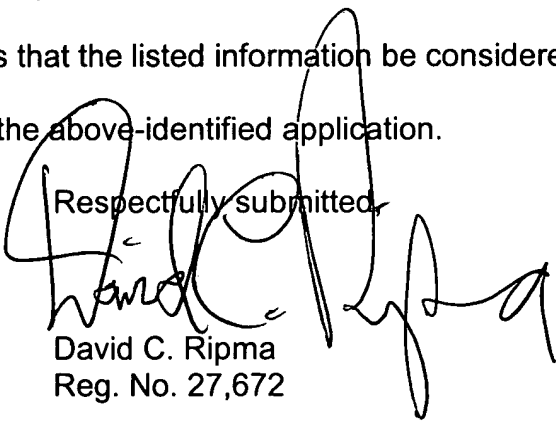
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

(Date) 2/23/04

Respectfully submitted,


David C. Ripma
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1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Complete If Known		
				Application Number		
				Filing Date	02/23/04	
				First Named Inventor	Fengyan Zhang	
				Group Art Unit		
LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary)				Examiner Name		
				Attorney Docket No.	SLA.0642	
Sheet	1	of	1			

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document Kind Number Code ² (if known)		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear
		6,288,420		Zhang et al.	09-11-01	
		6,236,113		Zhang et al.	05-22-01	
		6,190,963		Zhang et al.	02-20-01	

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T ⁶
		Office ³ Code ⁵	Number ⁴	Kind				

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²
		KIJIMA ET AL., Preparation of Bi ₄ Ti ₃ O ₁₂ thin films on Si (100) using Bi ₂ SiO ₅ buffer layer and its electric characterization, J. Appl. Phys. Vol 37, Pt 1, 9B, 5171 (1998)	
		NAKAMURA ET AL., Preparation of C-axis-oriented Bi ₄ Ti ₃ O ₁₂ thin films by metalorganic chemical vapor deposition, Jpn. J. Phys. Vol. 32, 4086 (1993)	

Examiner Signature		Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. ⁶Applicant is to place a check mark here if English language Translation is attached